

N-Channel Enhancement Mode Field Effect Transistor

General Description

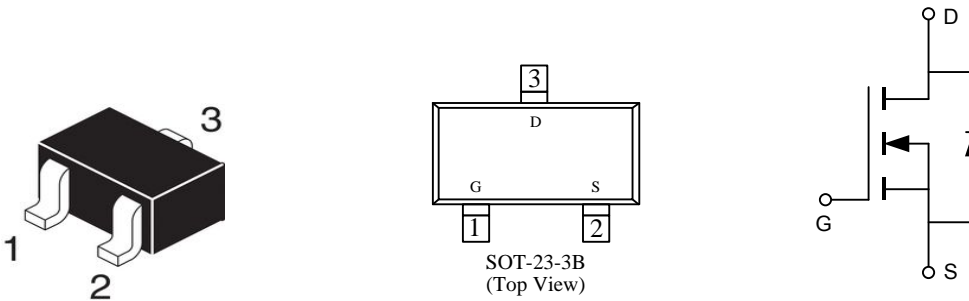
Product Summary		
V_{DSS}	I_D	$R_{DS(ON)}(m\Omega)TYP$
20V	0.65A	130 @ $V_{GS}= 4.5V$
	0.55A	160 @ $V_{GS}= 2.5V$

Features

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3B package

Package

- SOT-23-3B



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2306	-55°C to +150°C	SOT-23-3B	3000

Absolute Maximum Ratings

($T_A=25^\circ C$ unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DSS}	20	V
Gate-source voltage	V_{GSS}	± 8	V
Coutinuous drain current ($T_j=150^\circ C$)	I_D	$T_A=25^\circ C$	1.30
		$T_A=80^\circ C$	0.90
Pulsed drain current	I_{DM}	2.0	A
Drain-source Diode forward current	I_S	0.6	A
Power dissipation	P_D	$T_A=25^\circ C$	0.27
		$T_A=70^\circ C$	0.16
Operating junction Temperature range	T_j	-55—150	$^\circ C$